CLAIM(S):

1. A chemical-mechanical polishing composition comprising:

(a) wet-process silica,

(b) a combination of

(i) an alcohol of formula (I): $R^1–X–(CH_2)_m–OH$ wherein

R^1 is phenyl, pyridyl, $HO–(CH_2)_n–$, or C_1-C_6 alkyl,

m is an integer from 1 to 6,

n is an integer from 1 to 6, and

X is absent or is O, and

(ii) an alcohol of formula (II): $R^2–NR^3–(CH_2)_o–OH$ wherein

R^2 is phenyl, pyridyl, $H_2N–(CH_2)_p–$, or C_1-C_6 alkyl,

R^3 is hydrogen or C_1-C_6 alkyl,

o is an integer from 1 to 6, and

p is an integer from 1 to 6,

(c) hydrogen peroxide,

(d) a mineral acid, and

(e) water,

wherein the polishing composition has a pH from about 1 to about 5,

wherein the alcohol of formula (I) is phenoxyethanol, ethylene glycol monobutyl ether, or benzyl alcohol,

wherein the alcohol of formula (II) is aminoethylaminoethanol.

2. The polishing composition of claim 1, wherein the wet-process silica has a particle size of 5 nm to 25 nm.

3. The polishing composition of claim 2, wherein the wet-process silica has a particle size of 5 nm to 10 nm.

4. The polishing composition of claim 1, wherein the alcohol of formula (I) is phenoxyethanol.

5. The polishing composition of claim 1, wherein the polishing composition comprises 1000 ppm to 10,000 ppm of the alcohol of formula (I) and 100 ppm to 1000 ppm of the alcohol of formula (II).

6. The polishing composition of claim 1, wherein the polishing composition has a pH of 1 to 2.

7. A method of chemically mechanically polishing a substrate comprising:

(i) providing a substrate,

(ii) providing a polishing pad,

(iii) providing a chemical-mechanical polishing composition comprising:

(a) wet-process silica,

(b) a combination of

(i) an alcohol of formula (I): $R^1–X–(CH_2)_m–OH$ wherein

R^1 is phenyl, pyridyl, $HO–(CH_2)_n–$, or C_1-C_6 alkyl,

m is an integer from 1 to 6,

n is an integer from 1 to 6, and

X is absent or is O,

wherein the alcohol of formula (I) is phenoxyethanol, ethylene glycol monobutyl ether, or benzyl alcohol; and

(ii) an alcohol of formula (II): $R^2–NR^3–(CH_2)_o–OH$ wherein

R^2 is phenyl, pyridyl, $H_2N–(CH_2)_p–$, or C_1-C_6 alkyl,

R^3 is hydrogen or C_1-C_6 alkyl,

o is an integer from 1 to 6, and

p is an integer from 1 to 6,

wherein the alcohol of formula (II) is aminoethylaminoethanol,

(c) hydrogen peroxide,

(d) a mineral acid, and

(e) water

wherein the polishing composition has a pH from 1 to 5

(iv) contacting the substrate with the polishing pad and the chemical-mechanical polishing composition, and

(v) moving the polishing pad and the chemical mechanical polishing composition relative to the substrate to abrade at least a portion of the substrate to polish the substrate.

8. The method of claim 7, wherein the wet-process silica has a particle size of 5 nm to 25 nm.

9. The method of claim 7, wherein the polishing composition comprises 1000 ppm to 10,000 ppm of the alcohol of formula (I) and 100 ppm to 1000 ppm of the alcohol of formula (II).

10. The method of claim 7, wherein the substrate is a nickel-phosphorous-coated aluminum memory disk, and wherein at least a portion of the nickel-phosphorous is abraded to polish the substrate.

11. A method of chemically mechanically polishing a substrate comprising:

(i) providing a substrate,

(ii) providing a polishing pad,

(iii) providing a chemical-mechanical polishing composition comprising:

(a) wet-process silica,

(b) an alcohol of formula (III): $R^1–O–(CH_2)_m–OH$ wherein

R^1 is phenyl, pyridyl, $HO–(CH_2)_n–$, or C_1-C_6 alkyl,

m is an integer from 1 to 6, and

n is an integer from 1 to 6,

wherein the alcohol of formula (III) is phenoxyethanol, ethylene glycol monobutyl ether, or benzyl alcohol,

(c) hydrogen peroxide,

(d) a mineral acid, and

(e) water,

wherein the polishing composition has a pH from 1 to 5

(iv) contacting the substrate with the polishing pad and the chemical-mechanical polishing composition, and

(v) moving the polishing pad and the chemical mechanical polishing composition relative to the substrate to abrade at least a portion of the substrate to polish the substrate.

12. The method of claim 11, wherein the wet-process silica has a particle size of 5 nm to 25 nm.

13. The method of claim 13, wherein the polishing composition further comprises an alcohol of formula (II): $R^2–NR^3–(CH_2)_o–OH$ wherein R^2 is phenyl, pyridyl, $H_2N–(CH_2)_p–$, or C_1-C_6 alkyl, R^3 is hydrogen or C_1-C_6 alkyl, o is an integer from 1 to 6, and p is an integer from 1 to 6, wherein the alcohol of formula (II) is aminoethylaminoethanol.

14. The method of claim 13, wherein the polishing composition comprises 1000 ppm to 10,000 ppm of the alcohol of formula (III) and 100 ppm to 1000 ppm of the alcohol of formula (II).

15. The method of claim 11, wherein the substrate is a nickel-phosphorous-coated aluminum memory disk, and wherein at least a portion of the nickel-phosphorous is abraded to polish the substrate.